Silicon NPN Power Transistors BU2527AX

DESCRIPTION

- With TO-3PML package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of high resolution monitors

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

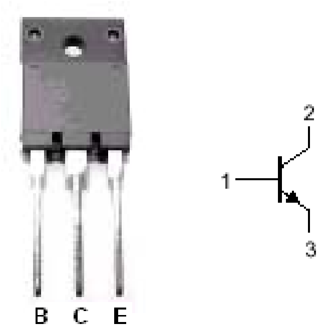

Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	V
I_C	Collector current (DC)		12	A
I_{CP}	Collector current (Pulse)		30	A
I_B	Base current (DC)		8	A
I_{BM}	Base current (Pulse)		12	A
P_{tot}	Total power dissipation	T_C=25℃	45	W
T_j	Max.operating junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0,L=25mH	800			V
V_{EBO}	Emitter-base breakdown voltage	I_B=1mA ;I_C=0	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=6A ;I_B=1.2A			5.0	V
V_{BEsat}	Emitter-base saturation voltage	I_C=6A ;I_B=1.2A			1.3	V
I_{CES}	Collector cut-off current	V_{CE}=$BV_{CES;}$ V_{BE}=0 T_C=125℃			0.25 2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7.5V; I_C=0			0.25	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	6		21	
h_{FE-2}	DC current gain	I_C=6A ; V_{CE}=5V	5		9	
C_C	Collector capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		145		pF

PACKAGE OUTLINE

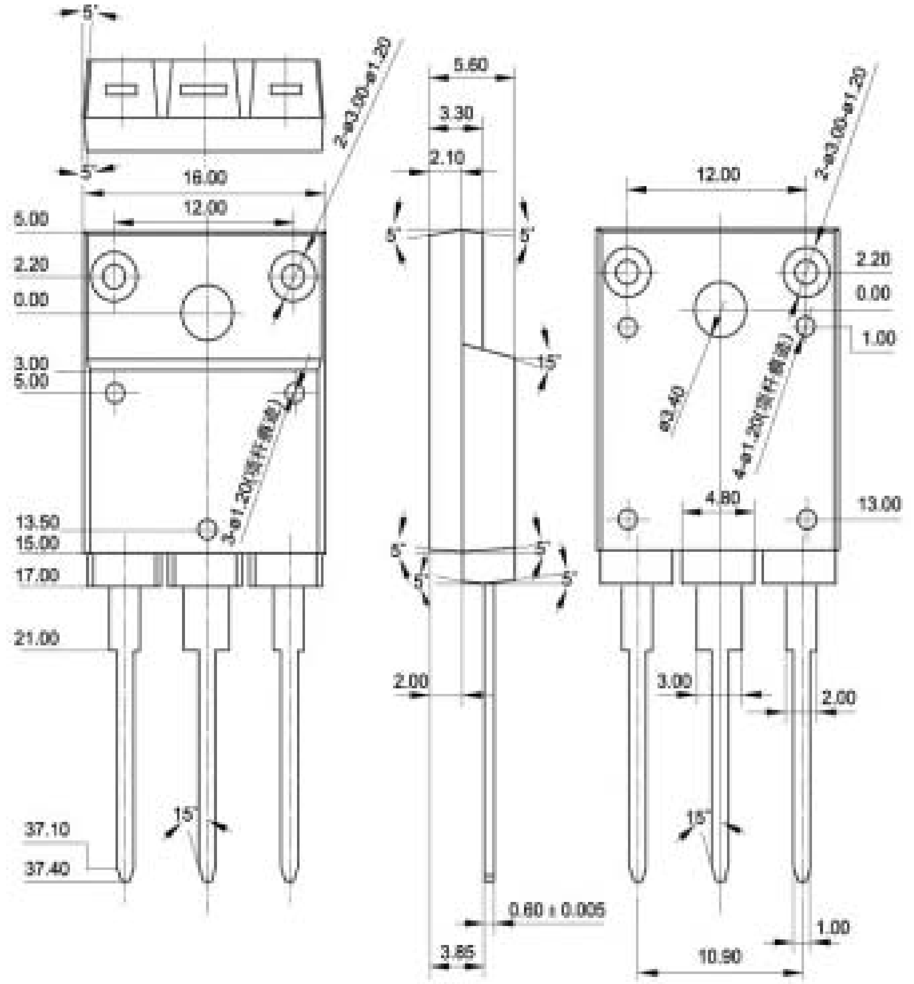

Fig.2 Outline dimensions